NSN 5961-01-272-8944

Photo Semiconductor Device - Page 1 of 2



View Online at https://aerobasegroup.com/nsn/5961-01-272-8944

Inclosure Material:
Metal and glass
Overall Length:
Between 0.225 inches and 0.255 inches
Terminal Length:
0.500 inches
Overall Diameter:
Between 0.209 inches and 0.230 inches
Function For Which Designed:
Phototransistor and amplifier
End Application:
Aegis
Internal Configuration:
Junction contact
Joint Electronic Device Engineering Council/jedec/case Outline Designation:
To-18
Mounting Method:
Terminal
Terminal Circle Diameter:
0.100 inches
Features Provided:
Hermetically sealed case
Semiconductor Material:
Gallium arsenide
Voltage Rating In Volts Per Characteristic:
25.0 collector to base voltage/static/emitter open and 25.0 collector to emitter voltage/static/base open and 5.0 emitter to collector voltage
dc
Current Rating Per Characteristic:
50.00 milliamperes peak forward surge current and 100.00 nanoamperes repetitive peak forward current peak
Power Rating Per Characteristic:
250.0 milliwatts small-signal input power, common-collector absolute
Maximum Operating Tempurature Per Measurement Point:
150.0 degrees celsius junction
Special Features:
Base lead 0.05 in. Max.; internal junction configuration: npn
Test Data Document:
53711-5366069 drawing (this is the basic governing drawing, such as a contractor drawing, original equipment manufacturer drawing, etc.
excludes any specification, standard or other document that may be referenced in a basic governing drawing)
Terminal Type And Quantity:
3 uninsulated wire lead
Shelf Life:
N/a

--

Unit Of Measure:

NSN 5961-01-272-8944

Photo Semiconductor Device - Page 2 of 2



Demilitarization:

Yes - demil/mli

Fiig:

A110a0